National Semiconductor

DM5400/DM7400 Quad 2-Input NAND Gates

General Description

This device contains four independent gates each of which performs the logic NAND function.

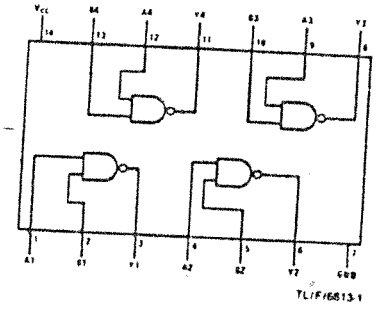
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6813-1

DM5400 (J) DM7400 (N)

Function Table

$Y = \overline{AB}$

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

H = High Logic Level
L = Low Logic Level

National Semiconductor

DM5402/DM7402 Quad 2-Input NOR Gates

General Description

This device contains four independent gates each of which performs the logic NOR function.

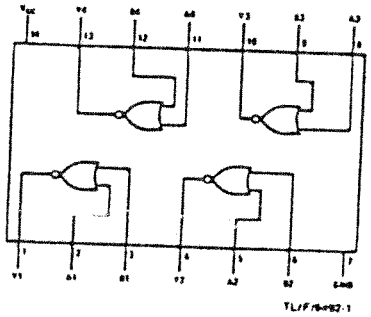
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/5402-1

DM5402 (J) DM7402 (N)

Function Table

$Y = \overline{A + B}$

Inputs		Output
A	B	Y
L	L	H
L	H	L
H	L	L
H	H	L

H = High Logic Level

L = Low Logic Level

National Semiconductor

DM5404/DM7404 Hex Inverting Gates

General Description

This device contains six independent gates each of which performs the logic INVERT function.

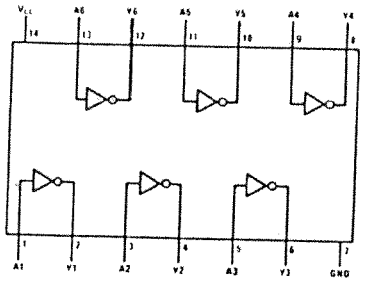
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6494-1

DM5404 (J) DM7404 (N)

Function Table

$Y = \overline{A}$

Input	Output
A	Y
L	H
H	L

H = High Logic Level

L = Low Logic Level

National Semiconductor

DM5408/DM7408 Quad 2-Input AND Gates

General Description

This device contains four independent gates each of which performs the logic AND function.

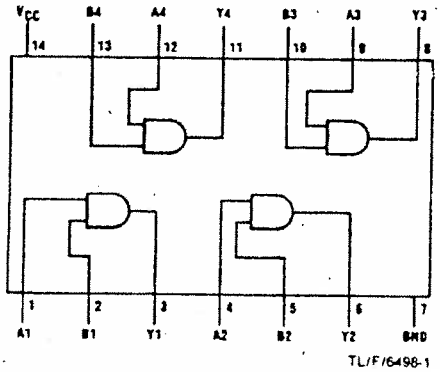
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6498-1

DM5408 (J) DM7408 (N)

Function Table

Y = AB

Inputs		Output
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

H = High Logic Level

L = Low Logic Level

National Semiconductor

DM5410/DM7410 Triple 3-Input NAND Gates

General Description

This device contains three independent gates each of which performs the logic NAND function.

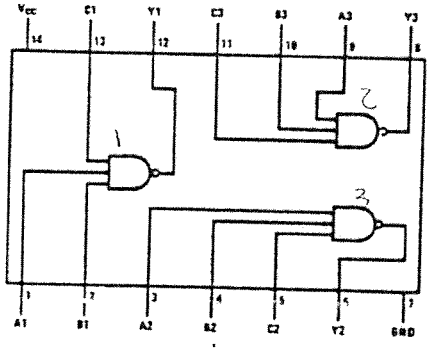
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6500-1

DM5410 (J) DM7410 (N)

Function Table

$Y = \overline{ABC}$

Inputs			Output
A	B	C	Y
X	X	L	H
X	L	X	H
L	X	X	H
H	H	H	L

H = High Logic Level
L = Low Logic Level
X = Either Low or High Logic Level

National Semiconductor

June 1989

54LS20/DM54LS20/DM74LS20 Dual 4-Input NAND Gates

General Description

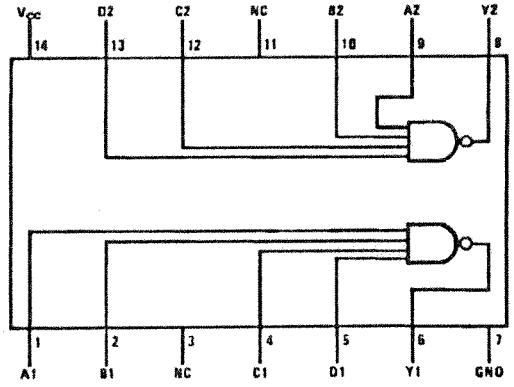
This device contains two independent gates each of which performs the logic NAND function.

Features

- Alternate Military/Aerospace device (54LS20) is available. Contact a National Semiconductor Sales Office/ Distributor for specifications

Connection Diagram

Dual-In-Line Package



TL/F/6355–1

Order Number 54LS20DMQB, 54LS20FMQB, 54LS20LMQB, DM54LS20J, DM54LS20W, DM74LS20M or DM74LS20N
See NS Package Number E20A, J14A, M14A, N14A or W14B

Function Table

$Y = \overline{ABCD}$

Inputs				Output
A	B	C	D	Y
X	X	X	L	H
X	X	L	X	H
X	L	X	X	H
L	X	X	X	H
H	H	H	H	L

H = High Logic Level
L = Low Logic Level
X = Either Low or High Logic Level

 TL/F/6355

National Semiconductor

DM5432/DM7432 Quad 2-Input OR Gates

General Description

This device contains four independent gates each of which performs the logic OR function.

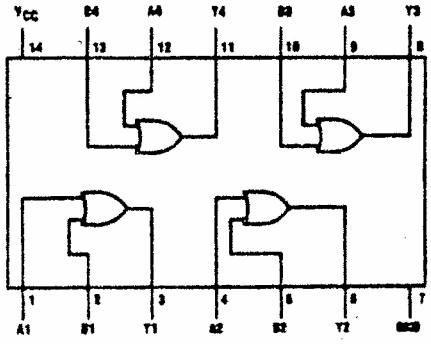
Absolute Maximum Ratings (Note

Supply Voltage
Input Voltage
Storage Temperature Range −65°C to

Note 1: The "Absolute Maximum Ratings" are those values which the safety of the device can not be guaranteed. The device not be operated at these limits. The parametric values defined "Electrical Characteristics" table are not guaranteed at the maximum ratings. The "Recommended Operating Conditions" define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6611-1

DM5432 (J) DM7432 (N)

Function Table

$Y = A + B$

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

H = High Logic Level
L = Low Logic Level

National Semiconductor

DM5473/DM7473 Dual Master-Slave J-K Flip-Flops with Clear, and Complementary Outputs

General Description

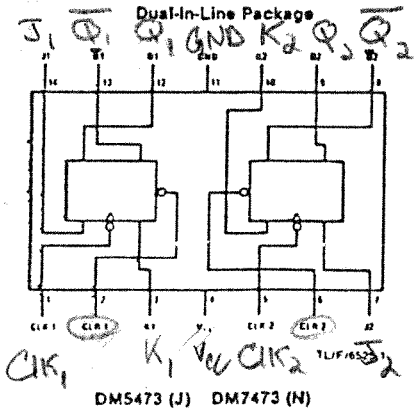
This device contains two independent positive pulse triggered J-K flip-flops with complementary outputs. The J and K data is processed by the flip-flops after a complete clock pulse. While the clock is low the slave is isolated from the master. On the positive transition of the clock, the data from the J and K inputs is transferred to the master. While the clock is high the J and K inputs are disabled. On the negative transition of the clock, the data from the master is transferred to the slave. The logic states of the J and K inputs must not be allowed to change while the clock is high. Data transfers to the outputs on the falling edge of the clock pulse. A low logic level on the clear input will reset the outputs regardless of the logic states of the other inputs.

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram



DM5473 (J) DM7473 (N)

Function Table

Inputs				Outputs	
CLR	CLK	J	K	Q	$\bar{Q}$
L	X	X	X	L	H
H	⎍	L	L	Q_0	$\bar{Q}_0$
H	⎍	H	L	H	L
H	⎍	L	H	L	H
H	⎍	H	H	Toggle	

H = High Logic Level

L = Low Logic Level

X = Either Low or High Logic Level

⎍ = Positive pulse data. The J and K inputs must be held constant while the clock is high. Data is transferred to the outputs on the falling edge of the clock pulse.

Q_0 = The output logic level before the indicated input conditions were established

Toggle = Each output changes to the complement of its previous level on each high level clock pulse

National Semiconductor

DM5474/DM7474 Dual Positive-Edge-Triggered D Flip-Flops with Preset, Clear and Complementary Outputs

General Description

This device contains two independent positive-edge-triggered D flip-flops with complementary outputs. The information on the D input is accepted by the flip-flops on the positive going edge of the clock pulse. The triggering occurs at a voltage level and is not directly related to the transition time of the rising edge of the clock. The data on the D input may be changed while the clock is low or high without affecting the outputs as long as the data setup and hold times are not violated. A low logic level on the preset or clear inputs will set or reset the outputs regardless of the logic levels of the other inputs.

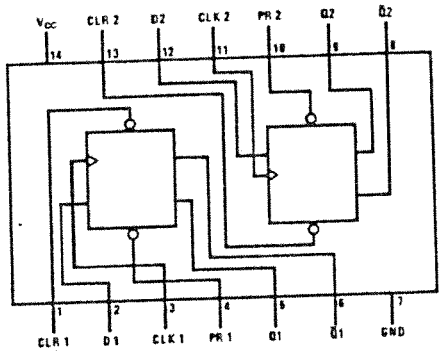
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6526-1

DM5474 (J) DM7474 (N)

Function Table

Inputs				Outputs	
PR	CLR	CLK	D	Q	$\overline{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H*	H*
H	H	↑	H	H	L
H	H	↑	L	L	H
H	H	L	X	Q_O	$\overline{Q}_O$

H = High Logic Level

X = Either Low or High Logic Level

L = Low Logic Level

↑ = Positive-going transition of the clock.

* = This configuration is nonstable; that is, it will not persist when either the preset and/or clear inputs return to their inactive (high) level.

Q_O = The output logic level of Q before the indicated input conditions were established.

National Semiconductor

DM5475/DM7475 Quad Latches

General Description

These latches are ideally suited for use as temporary storage for binary information between processing units and input/output or indicator units. Information present at a data (D) input is transferred to the Q input when the enable (G) is high, and the Q output will follow the data input as long as the enable remains high. When the enable goes low, the information (that was present at the data input at the time the transition occurred) is retained at the Q output until the enable is permitted to go high.

These latches feature complementary Q and $\overline{Q}$ outputs from a 4-bit latch and are available in 16-pin packages.

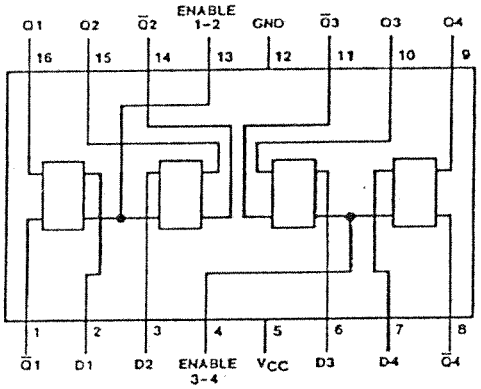
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6527-1

5475 (J) 7475 (N)

Function Table (Each Latch)

Inputs		Outputs	
D	G	Q	$\overline{Q}$
L	H	L	H
H	H	H	L
X	L	Q_0	$\overline{Q}_0$

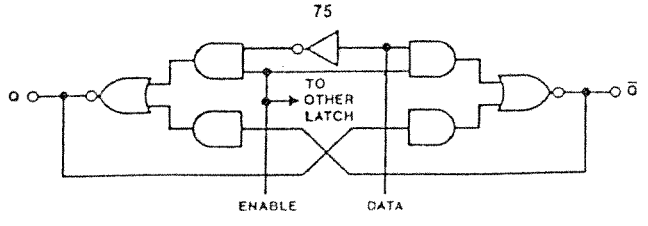
H = High Level

L = Low Level

X = Don't Care

Q_0 = The Level of Q Before the High-to-Low Transition of G

Logic Diagram (Each Latch)



TL/F/6527-2

National Semiconductor

DM5483/DM7483 4-Bit Binary Adders with Fast Carry

General Description

These full adders perform the addition of two 4-bit binary numbers. The sum (Σ) outputs are provided for each bit and the resultant carry (C4) is obtained from the fourth bit. These adders feature full internal look ahead across all four bits. This provides the system designer with partial look-ahead performance at the economy and reduced package count of a ripple-carry implementation.

The adder logic, including the carry, is implemented in its true form meaning that the end-around carry can be accomplished without the need for logic or level inversion.

Features

- Full-carry look-ahead across the four bits
- Systems achieve partial look-ahead performance with the economy of ripple carry
- Typical add times
  - Two 8-bit words 23 ns
  - Two 16-bit words 43 ns
- Typical power dissipation per 4-bit adder 290 mW

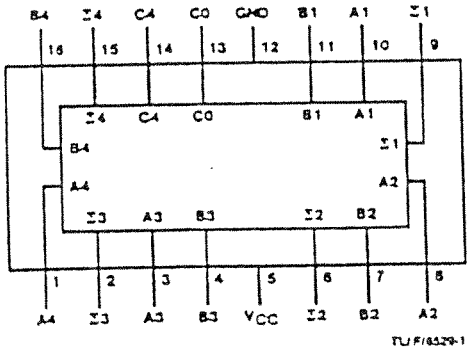
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6529-1

5483 (J) 7483 (N)

Function Table

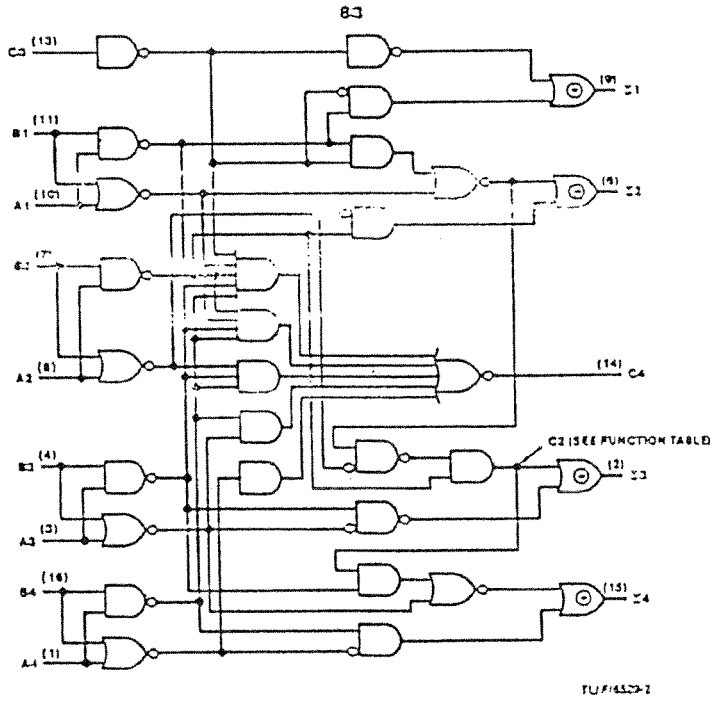
Inputs											
				Outputs							
				When C0 = L				When C0 = H			
				When C2 = L				When C2 = H			
A1 A3	B1 B3	A2 A4	B2 B4	Σ1	Σ3	Σ2 Σ4	C2 C4	Σ1	Σ3	Σ2 Σ4	C2 C4
L	L	L	L	L	L	L	L	H	L	L	L
H	L	L	L	H	L	L	L	L	L	L	L
L	H	L	L	H	L	L	L	L	L	L	L
H	H	L	L	L	L	L	L	H	L	L	L
L	L	H	L	H	L	L	L	L	L	L	L
H	L	H	L	L	L	L	L	H	L	L	L
L	H	H	L	L	L	L	L	H	L	L	L
H	H	H	L	H	L	L	L	L	L	L	L
L	L	L	H	H	L	L	L	L	L	L	L
H	L	L	H	L	L	L	L	H	L	L	L
L	H	L	H	L	L	L	L	H	L	L	L
H	H	L	H	H	L	L	L	L	L	L	L
L	L	H	H	L	L	L	L	H	L	L	L
H	L	H	H	H	L	L	L	L	L	L	L
L	H	H	H	H	L	L	L	L	L	L	L
H	H	H	H	L	H	H	H	H	H	H	H

H = High Level, L = Low Level

Note

Input conditions at A1, B1, A2, B2, and C0 are used to determine outputs Σ1 and Σ2 and the value of the internal carry C2. The values at C2, A3, B3, A4, and B4 are then used to determine outputs Σ3, Σ4, and C4.

Logic Diagram



TL/F/6529-2

National Semiconductor

DM5486/DM7486 Quad 2-Input Exclusive-OR Gates

General Description

This device contains four independent gates each of which performs the logic exclusive-OR function.

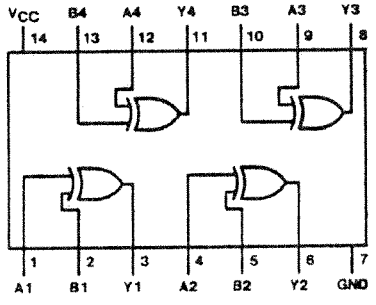
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6531-1

DM5486 (J) DM7486 (N)

Function Table

$Y = A \oplus B$

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

H = High Logic Level
L = Low Logic Level

National Semiconductor

DM54125/DM74125 Quad TRI-STATE® Buffers

General Description

This device contains four independent gates each of which performs a non-inverting buffer function. The outputs have the TRI-STATE feature. When enabled, the outputs exhibit the low impedance characteristics of a standard TTL output with additional drive capability at the high Logic level to permit the driving of bus lines without external pull-up resistors. When disabled, both the output transistors are turned off presenting a high-impedance state to the bus line. Thus the output will act neither as a significant load nor as a driver. To minimize the possibility that two outputs will attempt to take a common bus to opposite logic levels, the disable time is shorter than the enable time of the outputs.

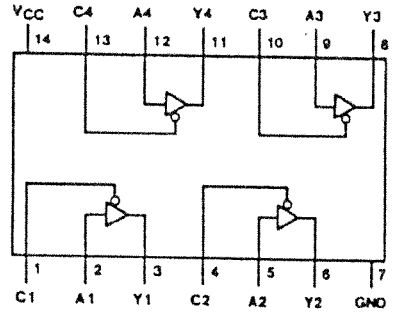
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6540-1

DM54125 (J) DM74125 (N)

Function Table

Y = A

Input		Output
A	C	Y
L	L	L
H	L	H
X	H	HI-Z

H = High Logic Level
L = Low Logic Level
X = Either Low or High Logic Level
HI-Z = TRI-STATE (Outputs are disabled)

National Semiconductor

DM54LS138/DM74LS138, DM54LS139/DM74LS139 Decoders/Demultiplexers

General Description

These Schottky-clamped circuits are designed to be used in high-performance memory-decoding or data-routing applications, requiring very short propagation delay times. In high-performance memory systems these decoders can be used to minimize the effects of system decoding. When used with high-speed memories, the delay times of these decoders are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The LS138 decodes one-of-eight lines, based upon the conditions at the three binary select inputs and the three enable inputs. Two active-low and one active-high enable inputs reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented with no external inverters, and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

The LS139 comprises two separate two-line-to-four-line decoders in a single package. The active-low enable input can be used as a data line in demultiplexing applications.

All of these decoders/demultiplexers feature fully buffered inputs, presenting only one normalized load to its driving circuit. All inputs are clamped with high-performance Schottky diodes to suppress line-ringing and simplify system design.

Features

- Designed specifically for high-speed:
  - Memory decoders
  - Data transmission systems
- LS138 3-to-8-line decoders incorporates 3 enable inputs to simplify cascading and/or data reception
- LS139 contains two fully independent 2-to-4-line decoders/demultiplexers
- Schottky clamped for high performance
- Typical propagation delay (3 levels of logic)
  - LS138 21 ns
  - LS139 21 ns
- Typical power dissipation
  - LS138 32 mW
  - LS139 34 mW

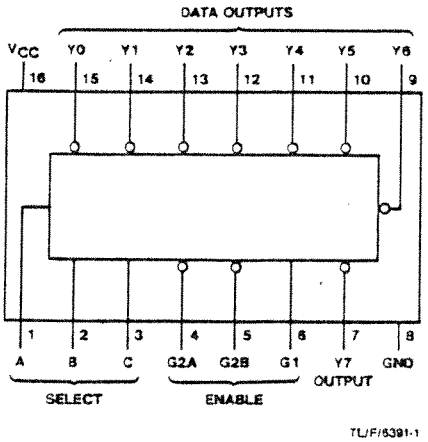
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	7V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagrams

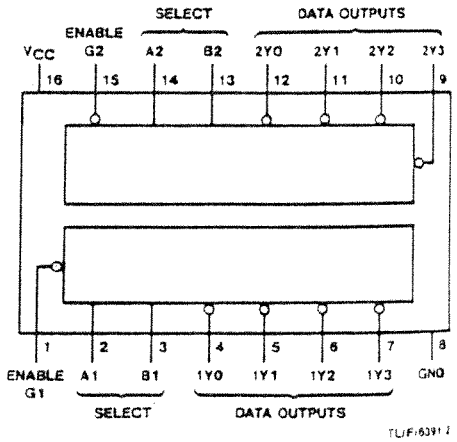
Dual-In-Line Package



TL/F/6391-1

54LS138 (J) 74LS138 (N)

Dual-In-Line Package



TL/F/6391-2

54LS139 (J) 74LS139 (N)

'LS139 Switching Characteristics at $V_{CC} = 5V$ and $T_A = 25°C$

(See Section 1 for Test Waveforms and Output Load)

Parameter	From (Input) To (Output)	$R_L = 2\ k\Omega$						Units
		$C_L = 15\ pF$			$C_L = 50\ pF$			
		Min	Typ	Max	Min	Typ	Max	
t_{PLH} Propagation Delay Time Low to High Level Output	Select to Output		13	18		16	27	ns
t_{PHL} Propagation Delay Time High to Low Level Output	Select to Output		17	27		23	40	ns
t_{PLH} Propagation Delay Time Low to High Level Output	Enable to Output		13	18		16	27	ns
t_{PHL} Propagation Delay Time High to Low Level Output	Enable to Output		16	24		22	40	ns

Function Tables

LS138

Inputs					Outputs							
Enable		Select										
G1	G2*	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	H	H	H	H	H	L	H	H	H	H
H	L	H	L	L	H	H	H	H	L	H	H	H
H	L	H	L	H	H	H	H	H	H	L	H	H
H	L	H	H	L	H	H	H	H	H	H	L	H
H	L	H	H	H	H	H	H	H	H	H	H	L

*G2 = G2A + G2B

H = High level, L = low level, X = don't care

LS139

Inputs			Outputs			
Enable	Select					
G	B	A	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

H = high level, L = low level, X = don't care

National Semiconductor

MM54HC151/MM74HC151 8-Channel Digital Multiplexer

microCMOS

General Description

This high speed Digital multiplexer utilizes micro-CMOS Technology, 3.5 micron silicon gate P-well CMOS. Along with the high noise immunity and low power dissipation of standard CMOS integrated circuits, it possesses the ability to drive 10 LS-TTL loads. The MM54HC151/MM74HC151 selects one of the 8 data sources, depending on the address presented on the A, B, and C inputs. It features both true (Y) and complement (W) outputs. The STROBE input must be at a low logic level to enable this multiplexer. A high logic level at the STROBE forces the W output high and the Y output low.

The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family.

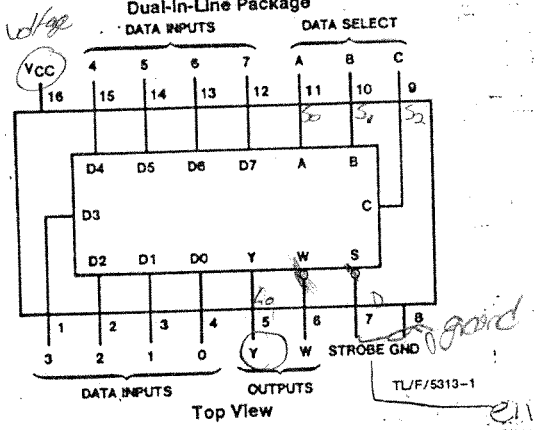
All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay
  data select to output Y: 26 ns
- Wide operating supply voltage range: 2–6V
- Low input current: <1 μA maximum
- Low quiescent supply current: 80 μA maximum (74HC)
- High output drive current: 4 mA minimum

Connection and Logic Diagrams

Dual-In-Line Package



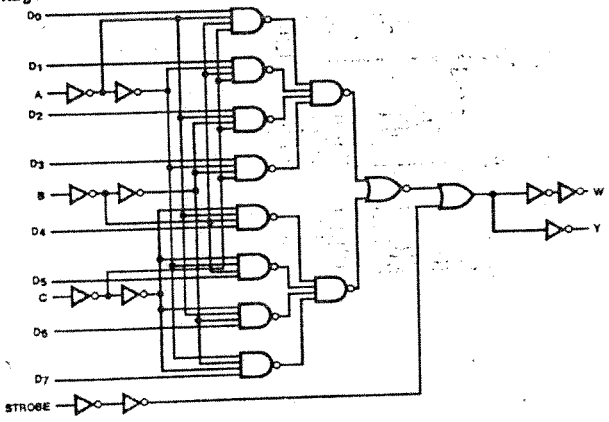
Top View

Order Number MM54HC151J or MM74HC151J, N
See NS Package J16A or N16E

Truth Table

Select C	Select B	Select A	Strobe S	Outputs Y	Outputs W
X	X	X	H	L	H
L	L	L	L	D0	$\overline{D0}$
L	L	H	L	D1	$\overline{D1}$
L	H	L	L	D2	$\overline{D2}$
L	H	H	L	D3	$\overline{D3}$
H	L	L	L	D4	$\overline{D4}$
H	L	H	L	D5	$\overline{D5}$
H	H	L	L	D6	$\overline{D6}$
H	H	H	L	D7	$\overline{D7}$

H = High Level, L = Low Level, X = Don't Care
D0, D1...D7 = the level of the respective D input



National Semiconductor

DM54153/DM74153 Dual 4-Line to 1-Line Data Selectors/Multiplexers

General Description

Each of these data selectors/multiplexers contains inverters and drivers to supply fully complementary, on-chip, binary decoding data selection to the AND-OR-invert gates. Separate strobe inputs are provided for each of the two four-line sections.

Features

- Permits multiplexing from N lines to 1 line
- Performs parallel-to-serial conversion
- Strobe (enable) line provided for cascading (N lines to n lines)
- High fan-out, low-impedance, totem-pole outputs
- Typical average propagation delay times
  - From data 11 ns
  - From strobe 18 ns
  - From select 20 ns
- Typical power dissipation 170 mW

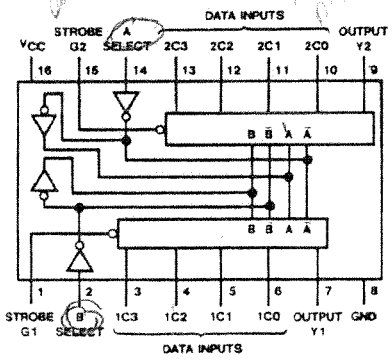
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6547-1

54153 (J) **74153 (N)**

Function Table

Select Inputs		Data Inputs				Strobe	Output
B	A	C0	C1	C2	C3	G	Y
X	X	X	X	X	X	H	L
L	L	L	X	X	X	L	L
L	L	H	X	X	X	L	H
L	H	X	L	X	X	L	L
L	H	X	H	X	X	L	H
H	L	X	X	L	X	L	L
H	L	X	X	H	X	L	H
H	H	X	X	X	L	L	L
H	H	X	X	X	H	L	H

Select inputs A and B are common to both sections.
H = High Level, L = Low Level, X = Don't Care

National Semiconductor

microCMOS

MM54HC157/MM74HC157 Quad 2-Input Multiplexer
MM54HC158/MM74HC158 Quad 2-Input Multiplexer (Inverted Output)

General Description

These high speed Quad 2-to-1 Line data selector/Multiplexers utilize microCMOS Technology, 3.5 micron silicon gate P-well CMOS. They possess the high noise immunity and low power consumption of standard CMOS integrated circuits, as well as the ability to drive 10 LS-TTL loads.

These devices each consist of four 2-input digital multiplexers with common select and STROBE inputs. On the MM54HC157/MM74HC157, when the STROBE input is at logical "0" the four outputs assume the values as selected from the inputs. When the STROBE input is at a logical "1" the outputs assume logical "0". The MM54HC158/MM74HC158 operates in the same manner, except that its outputs are inverted. Select decoding is done internally resulting in a single select input only. If enabled, the select input determines whether the A or B inputs get routed to their corresponding Y outputs.

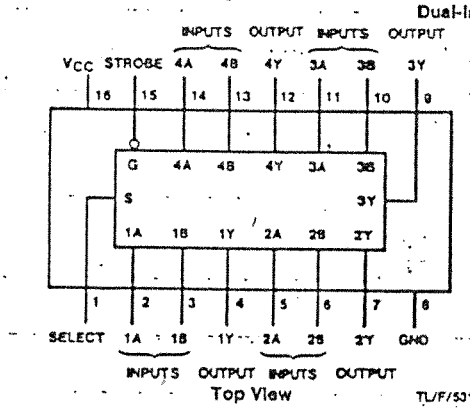
The 54HC/74HC logic family is functionally as well as pinout compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delay: 14 ns data to any output
- Wide power supply range: 2–6V
- Low power supply quiescent current: 80 μA maximum (74HC Series)
- Fan-out of 10 LS-TTL loads
- Low input current: 1 μA maximum

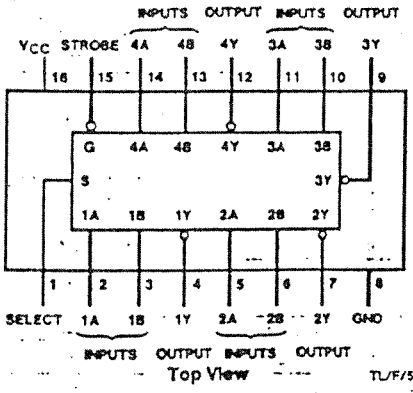
Connection Diagrams

Dual-In-Line Packages



Top View

TL/F/5314–1



Top View

TL/F/5314–2

Order Number MM54HC157J, MM54HC158J, MM74HC157J,N or MM74HC158J,N
See NS Package J16A or N16E

Function Table

Inputs				Output Y	
Strobe	Select	A	B	HC157	HC158
H	X	X	X	L	H
L	L	L	X	L	H
L	L	H	X	H	L
L	H	X	L	L	H
L	H	X	H	H	L

H = High Level, L = Low Level, X = Irrelevant

National Semiconductor

DM54194/DM74194 4-Bit Bidirectional Universal Shift Registers

General Description

These bidirectional shift registers are designed to incorporate virtually all of the features a system designer may want in a shift register; they feature parallel inputs, parallel outputs, right-shift and left-shift serial inputs, operating-mode-control inputs, and a direct overriding clear line. The register has four distinct modes of operation, namely:

Parallel (broadside) load
Shift right (in the direction Q_A toward Q_D)
Shift left (in the direction Q_D toward Q_A)
Inhibit clock (do nothing)

Synchronous parallel loading is accomplished by applying the four bits of data and taking both mode control inputs, S0 and S1, high. The data are loaded into the associated flip-flops and appear at the outputs after the positive transition of the clock input. During loading, serial data flow is inhibited.

Shift right is accomplished synchronously with the rising edge of the clock pulse when S0 is high and S1 is low. Serial data for this mode is entered at the shift-right data input. When S0 is low and S1 is high, data shifts left synchronously and new data is entered at the shift-left serial input.

Clocking of the flip-flop is inhibited when both mode control inputs are low. The mode controls of the of the DM54194/DM74194 should be changed only while the clock input is high.

Features

- Parallel inputs and outputs
- Four operating modes:
  - Synchronous parallel load
  - Right shift
  - Left shift
  - Do nothing
- Positive edge-triggered clocking
- Direct overriding clear
- Typical clock frequency 36 MHz
- Typical power dissipation 195 mW

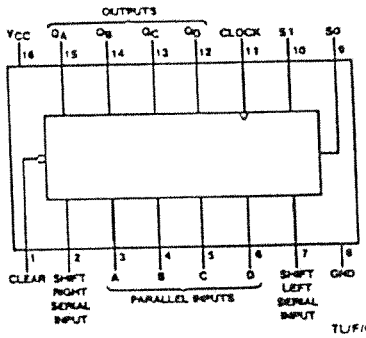
Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Storage Temperature Range	−65°C to 150°C

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device can not be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Connection Diagram

Dual-In-Line Package



TL/F/6564-1

54194 (J) 74194 (N)

Function Table

Inputs										Outputs			
Clear	Mode		Clock	Serial		Parallel				Q_A	Q_B	Q_C	Q_D
	S1	S0		Left	Right	A	B	C	D				
L	X	X	X	X	X	X	X	X	X	L	L	L	L
H	X	X	L	X	X	X	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}
H	H	H	↑	X	X	a	b	c	d	a	b	c	d
H	L	H	↑	X	H	X	X	X	X	H	Q_{An}	Q_{Bn}	Q_{Cn}
H	L	H	↑	X	L	X	X	X	X	L	Q_{An}	Q_{Bn}	Q_{Cn}
H	H	L	↑	H	X	X	X	X	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	H
H	H	L	↑	L	X	X	X	X	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	L
H	L	L	X	X	X	X	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}

H = High Level (steady state), L = Low Level (steady state), X = Don't Care (any input, including transitions)

↑ = Transition from low to high level

a, b, c, d = The level of steady state input at inputs A, B, C, or D, respectively.

Q_{A0}, Q_{B0}, Q_{C0}, Q_{D0} = The level of Q_A, Q_B, Q_C, or Q_D, respectively, before the indicated steady state input conditions were established.

Q_{An}, Q_{Bn}, Q_{Cn}, Q_{Dn} = The level of Q_A, Q_B, Q_C, respectively, before the most-recent ↑ transition of the clock.

intel

2114A
1024 X 4 BIT STATIC RAM

	2114AL-1	2114AL-2	2114AL-3	2114AL-4	2114A-4	2114A-5
Max. Access Time (ns)	100	120	150	200	200	250
Max. Current (mA)	40	40	40	40	70	70

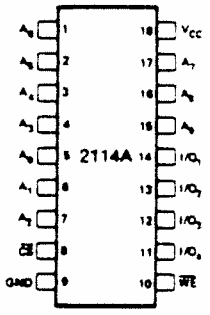
- **HMOS Technology**
- **Low Power, High Speed**
- **Identical Cycle and Access Times**
- **Single +5V Supply ±10%**
- **High Density 18 Pin Package**
- **Completely Static Memory - No Clock or Timing Strobe Required**
- **Directly TTL Compatible: All Inputs and Outputs**
- **Common Data Input and Output Using Three-State Outputs**
- **Available in EXPRESS**
  - — Standard Temperature Range
  - — Extended Temperature Range

The Intel® 2114A is a 4096-bit static Random Access Memory organized as 1024 words by 4-bits using HMOS, a high performance MOS technology. It uses fully DC stable (static) circuitry throughout, in both the array and the decoding, therefore it requires no clocks or refreshing to operate. Data access is particularly simple since address setup times are not required. The data is read out nondestructively and has the same polarity as the input data. Common input/output pins are provided.

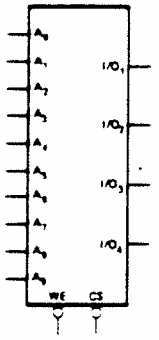
The 2114A is designed for memory applications where the high performance and high reliability of HMOS, low cost, large bit storage, and simple interfacing are important design objectives. The 2114A is placed in an 18-pin package for the highest possible density.

It is directly TTL compatible in all respects: inputs, outputs, and a single +5V supply. A separate Chip Select ($\overline{CS}$) lead allows easy selection of an individual package when outputs are or-tied

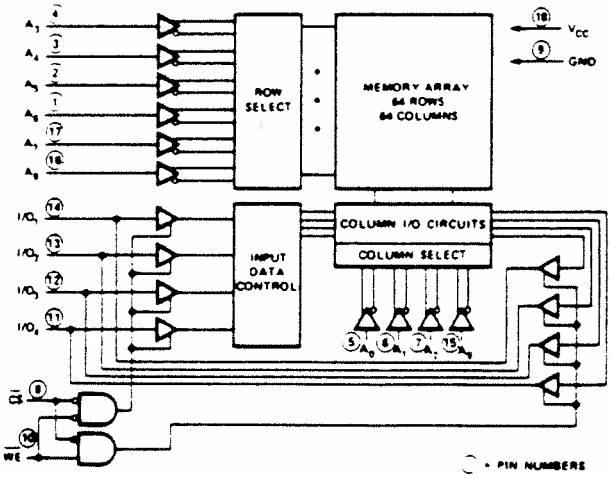
PIN CONFIGURATION



LOGIC SYMBOL



BLOCK DIAGRAM



PIN NAMES

A_0–A_9	ADDRESS INPUTS	V_{CC}	POWER (+5V)
$\overline{WE}$	WRITE ENABLE	GND	GROUND
$\overline{CS}$	CHIP SELECT		
I/O_1–I/O_4	DATA INPUT/OUTPUT		

Figure 5-11
2114A (1024 × 4-Bit) Static RAM Data Sheet
(Reprinted by permission of Intel Corporation, © 1983, Intel Corporation.)

2114A FAMILY

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	-10°C to 80°C
Storage Temperature	-65°C to 150°C
Voltage on any Pin With Respect to Ground	-3.5V to +7V
Power Dissipation	1.0W
D.C. Output Current	5mA

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. AND OPERATING CHARACTERISTICS

T_A = 0°C to 70°C, V_{CC} = 5V ± 10%, unless otherwise noted.

SYMBOL	PARAMETER	2114AL-1/L-2/L-3/L-4 Min.	Typ.[1]	Max.	2114A-4/-5 Min.	Typ.[1]	Max.	UNIT	CONDITIONS
I_{LI}	Input Load Current (All Input Pins)		.01	1			1	µA	V_{IN} = 0 to 5.5V
I_{LO}	I/O Leakage Current		1	10			10	µA	$\overline{CS}$ = V_{IH}, $V_{I/O}$ = 0 to 5.5
I_{CC}	Power Supply Current		25	40		50	70	mA	V_{CC} = max, $I_{I/O}$ = 0 mA, T_A = 0°C
V_{IL}	Input Low Voltage	-3.0		0.8	-3.0		0.8	V	
V_{IH}	Input High Voltage	2.0		6.0	2.0		6.0	V	
I_{OL}	Output Low Current	4.0	9.0		4.0	9.0		mA	V_{OL} = 0.4V
I_{OH}	Output High Current	-2.0	-2.5		-2.0	-2.5		mA	V_{OH} = 2.4V
I_{OS}[2]	Output Short Circuit Current			40			40	mA	V_{OUT} = GND

NOTE: 1. Typical values are for T_A = 25°C and V_{CC} = 5.0V
2. Duration not to exceed 1 second

CAPACITANCE

T_A = 25°C, f = 1.0 MHz

SYMBOL	TEST	MAX	UNIT	CONDITIONS
$C_{I/O}$	Input/Output Capacitance	5	pF	$V_{I/O}$ = 0V
C_{IN}	Input Capacitance	5	pF	V_{IN} = 0V

NOTE: This parameter is periodically sampled and not 100% tested.

A.C. CONDITIONS OF TEST

Input Pulse Levels	0.8 Volt to 2.0 Volt
Input Rise and Fall Times	10 nsec
Input and Output Timing Levels	0.8 Volts to 2.0 Volts
Output Load	1 TTL Gate and C_L = 100 pF

LOAD FOR T_{OTD} AND T_{OTW}

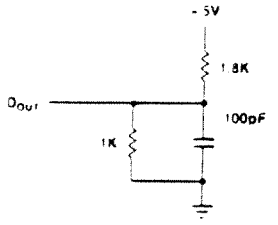


Figure 1.

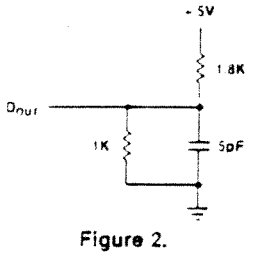


Figure 2.

Figure 5-11
2114A (1024 × 4-Bit) Static RAM Data Sheet
(Reprinted by permission of Intel Corporation. © 1983, Intel Corporation.)

2114A FAMILY

A.C. CHARACTERISTICS T_A = 0°C to 70°C, V_{CC} = 5V ± 10%, unless otherwise noted.

READ CYCLE [1]

SYMBOL	PARAMETER	2114AL-1 Min.	2114AL-1 Max.	2114AL-2 Min.	2114AL-2 Max.	2114AL-3 Min.	2114AL-3 Max.	2114A-4/L-4 Min.	2114A-4/L-4 Max.	2114A-5 Min.	2114A-5 Max.	UNIT
t_{RC}	Read Cycle Time	100		120		150		200		250		ns
t_A	Access Time		100		120		150		200		250	ns
t_{CO}	Chip Selection to Output Valid		70		70		70		70		85	ns
t_{CX} [3]	Chip Selection to Output Active	10		10		10		10		10		ns
t_{OTD} [3]	Output 3-state from Deselection		30		35		40		50		60	ns
t_{OHA}	Output Hold from Address Change	15		15		15		15		15		ns

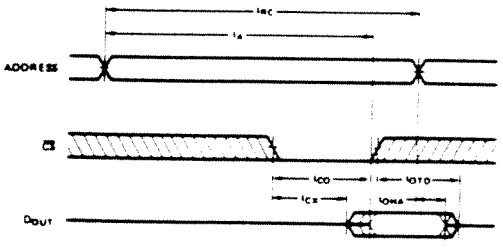
WRITE CYCLE [2]

SYMBOL	PARAMETER	2114AL-1 Min.	2114AL-1 Max.	2114AL-2 Min.	2114AL-2 Max.	2114AL-3 Min.	2114AL-3 Max.	2114A-4/L-4 Min.	2114A-4/L-4 Max.	2114A-5 Min.	2114A-5 Max.	UNIT
t_{WC}	Write Cycle Time	100		120		150		200		250		ns
t_W	Write Time	75		75		90		120		135		ns
t_{WR}	Write Release Time	0		0		0		0		0		ns
t_{OTW} [3]	Output 3-state from Write		30		35		40		50		60	ns
t_{DW}	Data to Write Time Overlap	70		70		90		120		135		ns
t_{DH}	Data Hold from Write Time	0		0		0		0		0		ns

NOTES:
1. A Read occurs during the overlap of a low $\overline{CS}$ and a high $\overline{WE}$.
2. A Write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$. t_W is measured from the latter of $\overline{CS}$ or $\overline{WE}$ going low to the earlier of $\overline{CS}$ or $\overline{WE}$ going high.
3. Measured at ± 500 mV with 1 TTL Gate and C_L = 500 pF.

WAVEFORMS

READ CYCLE ③



NOTES:
3. $\overline{WE}$ is high for a Read Cycle.
4. If the $\overline{CS}$ low transition occurs simultaneously with the $\overline{WE}$ low transition, the output buffers remain in a high impedance state.
5. $\overline{WE}$ must be high during all address transitions.

WRITE CYCLE

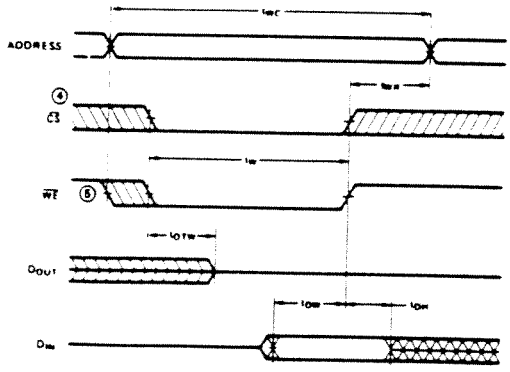


Figure 5-11
2114A (1024 × 4-Bit) Static RAM Data Sheet
(Reprinted by permission of Intel Corporation. © 1983, Intel Corporation.)